

## **Initial Information Data Sheet**

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### **Inventor Information**

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### **Correspondence Information**

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### **Application Information**

Title Line One::	Gallium Nitride Semiconductor Light
Title Line Two::	Emitting Device Having Multi-Quantum
Title Line Three::	-Well Structure Active Layer, And
Title Line Four::	Semiconductor Laser Light Source Device
Total Drawing Sheets::	10
Formal Drawings?::	Yes
Application Type::	Utility
Docket Number::	204552016410

### **Representative Information**

Representative Customer Number::	25227
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## Continuity Information

This application is a::  
> Application One::  
Filing Date::

Continuation of  
09/380,537  
September 2, 1999

which is a::  
>>Application Two::  
Filing Date::

371 of  
PCT/JP98/00828  
February 27, 1998

## Prior Foreign Applications

Foreign Application One::  
Filing Date::  
Country::  
Priority Claimed::

JP 9-52596  
March 7, 1997  
Japan  
Yes

Foreign Application Two::  
Filing Date::  
Country::  
Priority Claimed::

JP 9-65725  
March 19, 1997  
Japan  
Yes